

Band switching diode

Features

1. Low differential forward resistance
2. Low diode capacitance
3. High reverse impedance

Applications

Band switching in VHF-tuners

Construction

Silicon epitaxial planar

Absolute Maximum Ratings

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	35	V
Forward current		I_F	100	mA
Junction temperature		T_j	150	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-55...+150	$^{\circ}\text{C}$

Maximum Thermal Resistance

$T_j=25^{\circ}\text{C}$

Parameter	Test Conditions	Symbol	Value	Unit
Junction ambient	$l=4\text{mm}, T_L=\text{constant}$	R_{thJA}	350	K/W

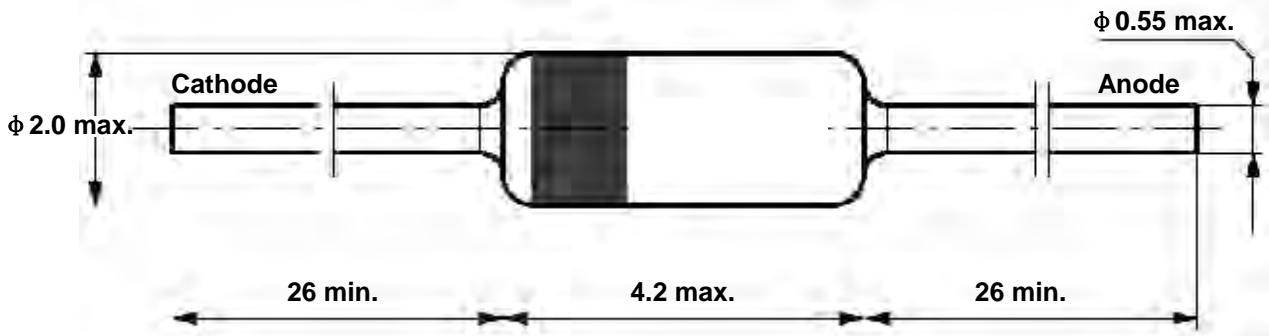
Electrical Characteristics

T_j=25°C

Parameter	Test Conditions	Type	Symbol	Min	Typ	Max	Unit
Forward voltage	I _F =100mA		V _F			1	V
Reverse current	V _R =20V		I _R			50	nA
Diode capacitance	f=100MHz, V _R =1V	BA282	C _D			1.5	pF
		BA283	C _D			1.2	pF
	f=100MHz, V _R =3V						
Differential forward resistance	f=200MHz, I _F =3mA	BA282	r _f			0.7	
		BA283	r _f			1.2	
	f=200MHz, I _F =10mA	BA282	r _f			0.5	
		BA283	r _f			0.9	
Reverse impedance	f=100MHz, V _R =1V		Z _r	100			K

Dimensions in mm

Cathode identification



Standard Glass Case
JEDEC DO 35